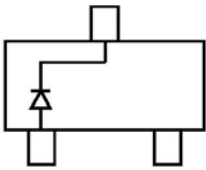


SCHOTTKY DIODE

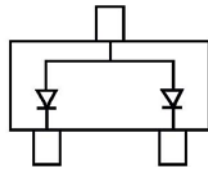
FEATURES

- Low Forward Voltage
- Fast Switching

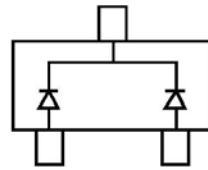
SOT-323



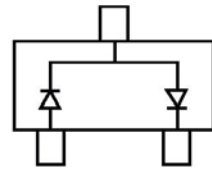
BAS40W MARKING: 43•



BAS40W-06 MARKING: 46



BAS40W-05 MARKING: 45



BAS40W-04 MARKING: 44

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak repetitive peak reverse voltage	V _{RRM}	40	V
Working peak reverse voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Forward continuous Current	I _{FM}	200	mA
Power Dissipation	P _D	150	mW
Thermal Resistance. Junction to Ambient Air	R _{θJA}	833	°C/W
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-65-125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 10μA	40		V
Reverse voltage leakage current	I _R	V _R =30V		200	nA
Forward voltage	V _F	I _F =1mA I _F =40mA		380 1000	mV
Diode capacitance	C _D	V _R =0, f=1MHz		5	pF
Reverse Recovery time	t _{rr}	I _r =1mA, I _R =I _F =10mA R _L =100Ω		5	nS

Typical Characteristics

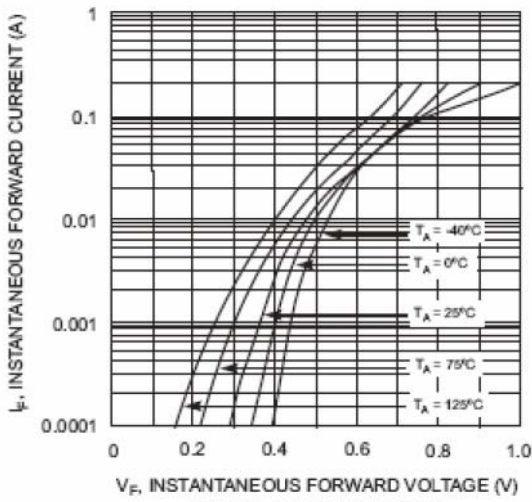


Fig. 1 Typical Forward Voltage

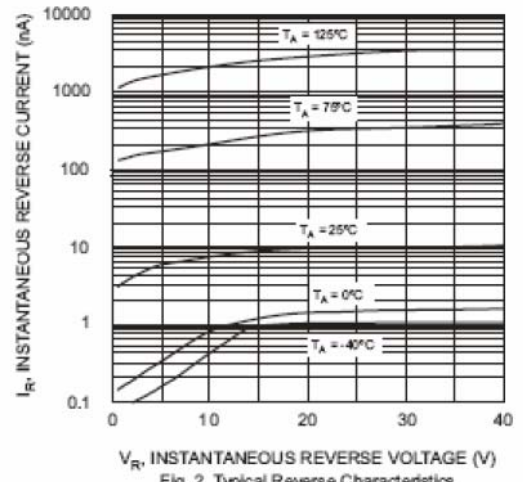


Fig. 2 Typical Reverse Characteristics

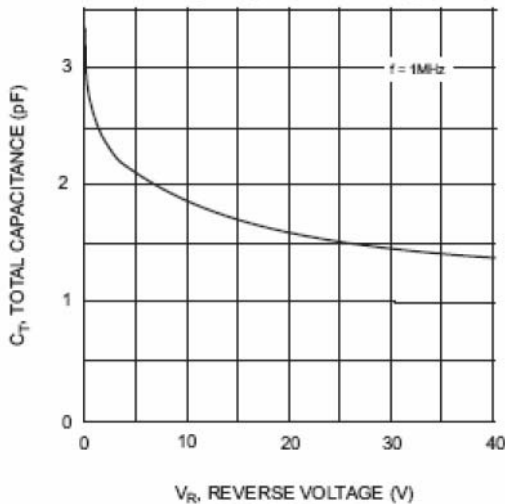


Fig. 3 Typical Capacitance

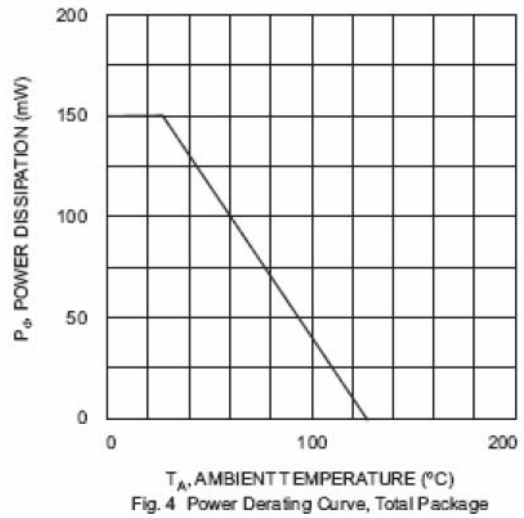


Fig. 4 Power Derating Curve, Total Package